

FIG. 1A

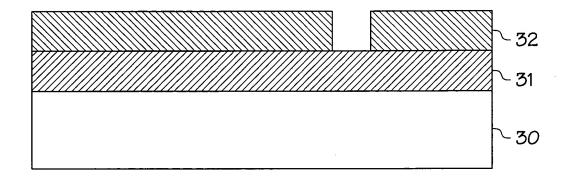


FIG. 1B

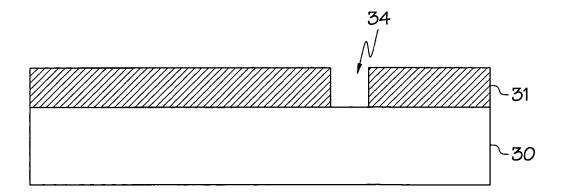


FIG. 1C

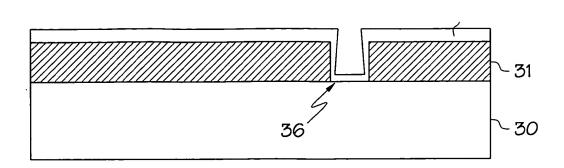


FIG. 1D

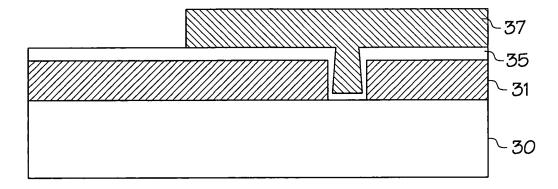


FIG. 1E

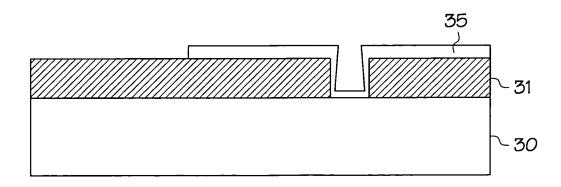


FIG. 1F

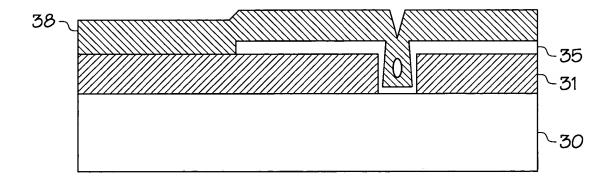


FIG. 1G

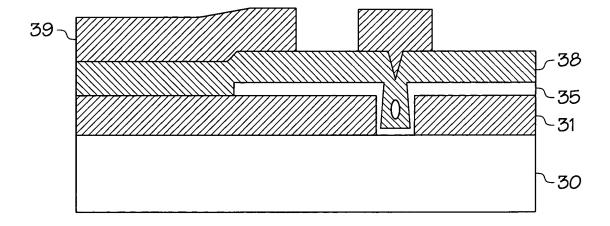


FIG. 1H

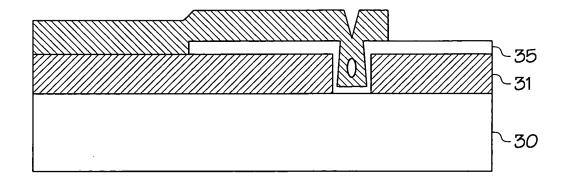


FIG. 11

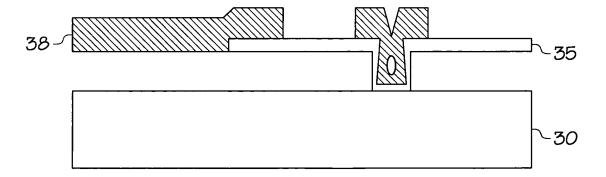


FIG. 1J

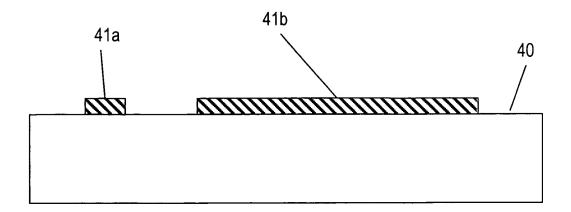


FIG. 2A

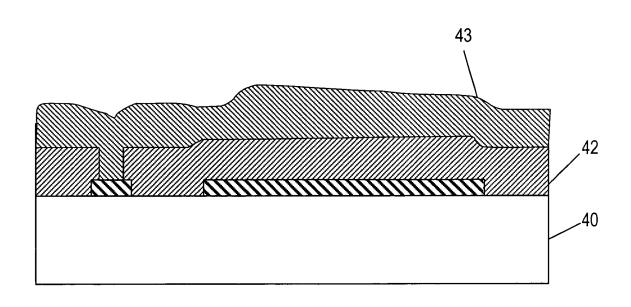


FIG. 2B

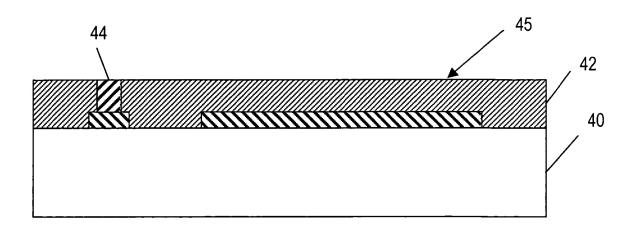


FIG. 2C

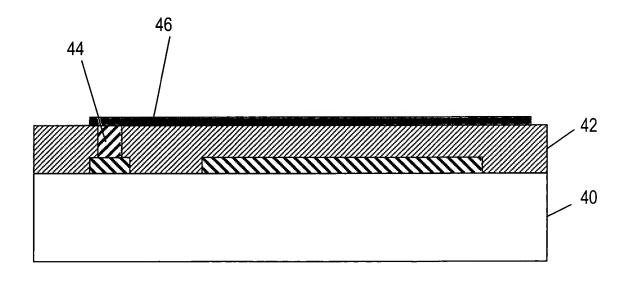


FIG. 2D

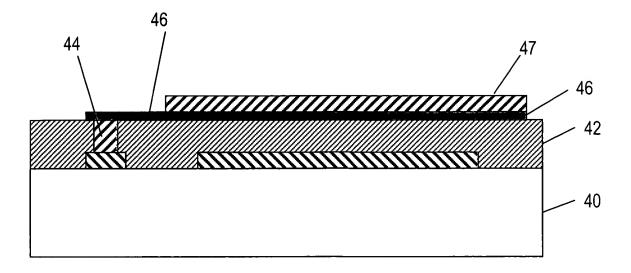


FIG. 2E

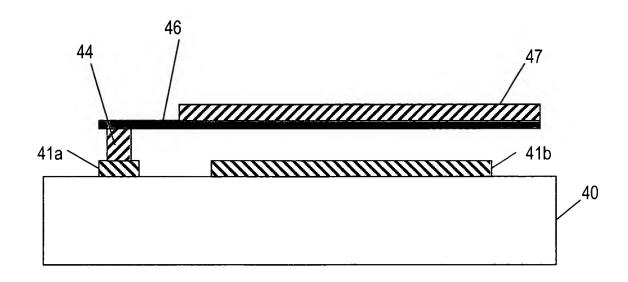


FIG. 2F

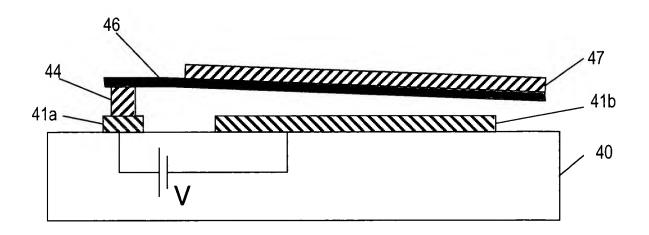


FIG. 2G

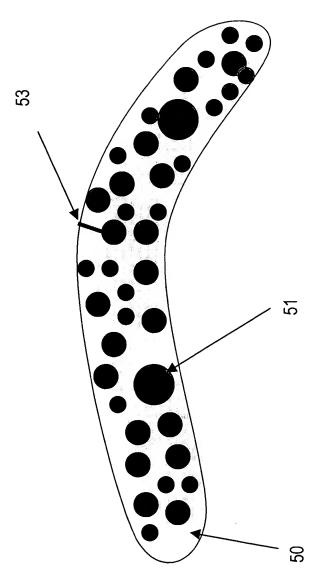
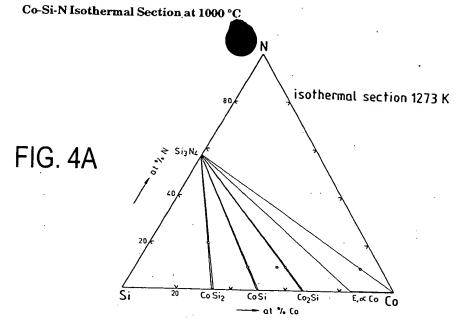
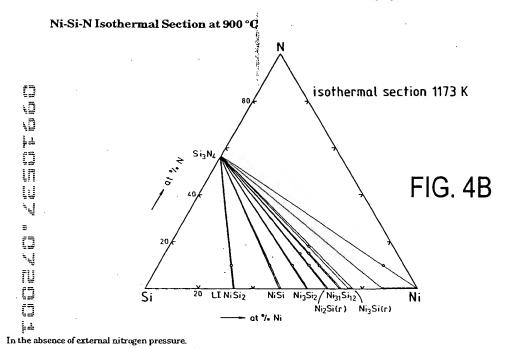


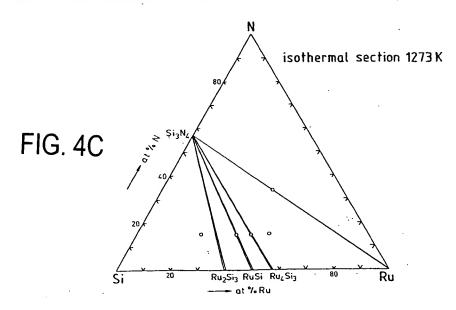
FIG. 3

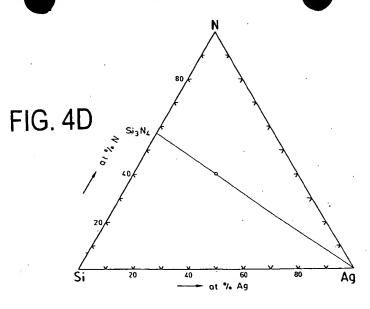


In the absence of external nitrogen pressure.

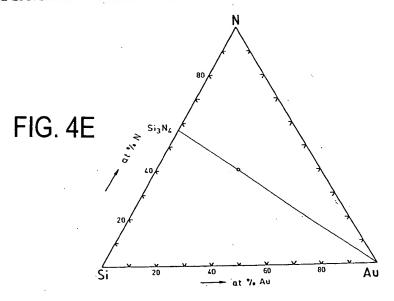


Ru-Si-N Isothermal Section at 1000 °C

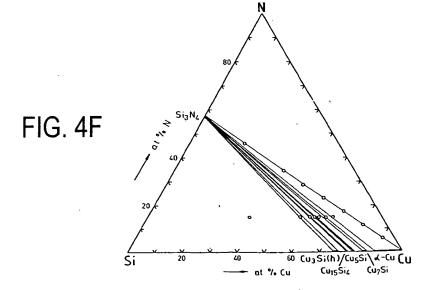


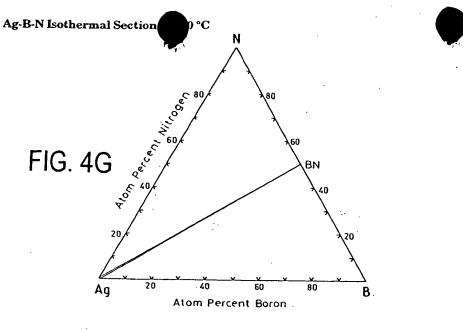


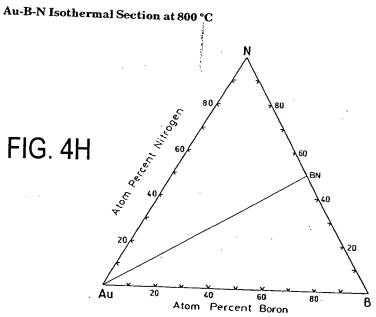
Au-Si-N Isothermal Section at 900 °C



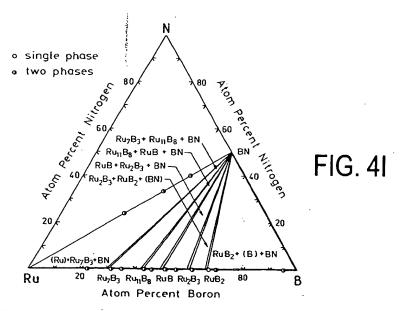
Cu-Si-N Isothermal Section at 700 °C

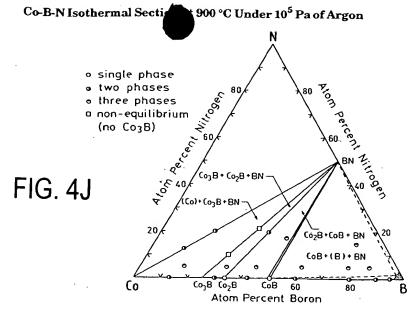






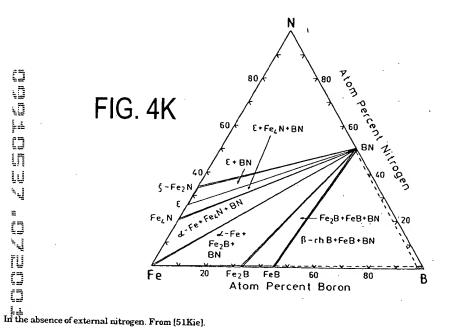
Ru-B-N Isothermal Section at 1200 °C Under 10⁵ Pa of Argon





Fe-B-N Isothermal Section at 400 °C

In the absence of external nitrogen.



Ni-B-N Isothermal Section at 900 °C Under 10⁵Pa of Argon

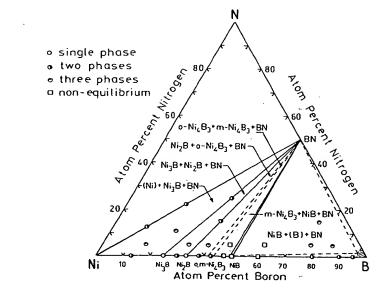


FIG 4L

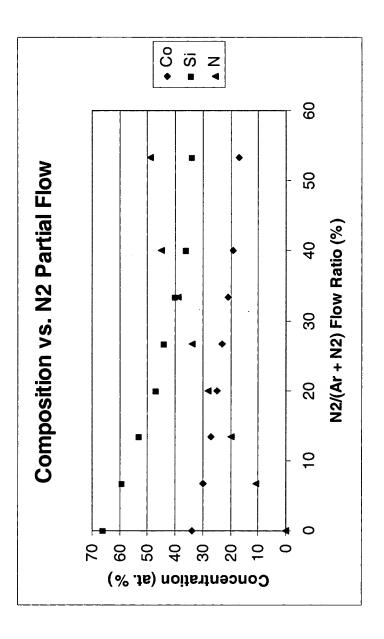


FIG. 5

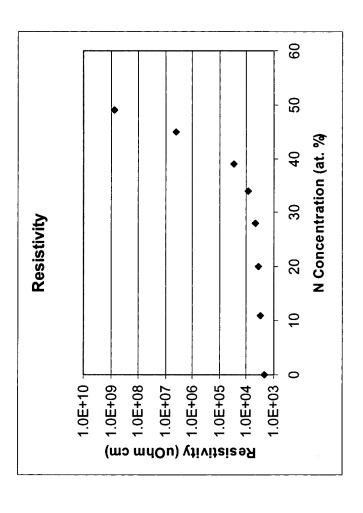


FIG. 6

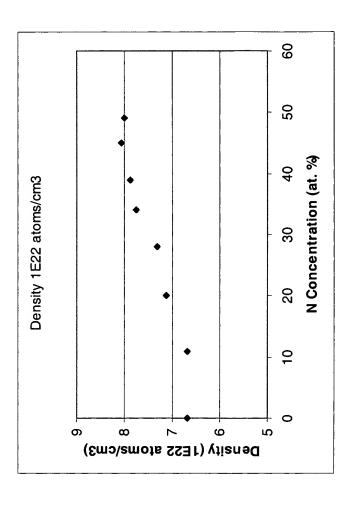


FIG. 7

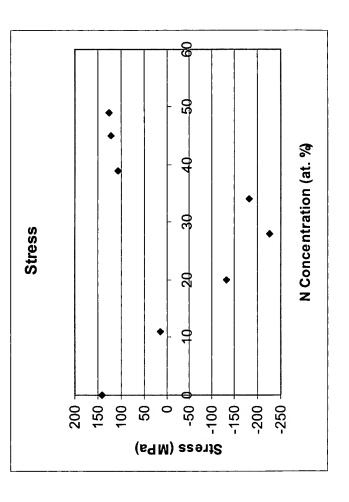


FIG. 8

	Cl2 base	F4 base	(nim)	220	180	160 t	! ○ ○
10 sccm	200	133					10 sccm
20 sccm	230	202	Etching rat				
30 sccm	270	202	Etching rate comparasion				20 sccm 30 sccm
			-C12 base -CF4 base				

FIG. 9

N2 in CoSiN